

TO-92L Plastic-Encapsulate Transistors

3CG8551 TRANSISTOR (PNP)

FEATURES

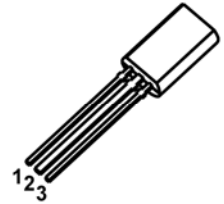
- General Purpose Switching Application
- Complementary to 3DG8051

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-40	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-2	A
P_C	Collector Power Dissipation	750	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	167	$^{\circ}\text{C/W}$
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$

TO – 92L

1. EMITTER
2. COLLECTOR
3. BASE



ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}, I_E=0$				V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10\text{mA}, I_B=0$				V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu\text{A}, I_C=0$				V
Collector cut-off current	I_{CBO}	$V_{CB}=-50\text{V}, I_E=0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=-40\text{V}, I_B=0$			-2	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-2\text{V}, I_C=-0.1\text{A}$	100	320		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-1\text{A}, I_B=-0.1\text{A}$			-1	V
Transition frequency	f_T	$V_{CE}=-10\text{V}, I_C=-50\text{mA}, f=100\text{MHz}$	150			MHz